

S60	707428	inert adj\$2 etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:28
S61	250293	S60 with gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:29
S62	2642927	plasma adj\$2 etch with inert adj\$2 gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:30
S63	1028277	inert adj\$2 plasma adj\$2 etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:30
S64	258	inert adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:31
S65	0	inert adj plasma with S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:32
S66	0	inert adj plasma with S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:32
S67	18	S64 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:38
S68	0	inert adj plasma adj etch with in-situ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:39
S69	0	inert adj plasma with etch with in-situ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:39

S70	258	inert adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:55
S71	40214	in-situ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:39
S72	40	S70 and S71	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:39
S73	33	S72 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:46
S79	7	etch with defect with S20	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 11:54
S80	0	(S70 with in-situ).ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 11:55
S83	63211	plasma with treat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:57
S84	25937	(plasma with treat\$5).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:58
S85	8	S84 with string\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:58
S86	2	S84 with poly with defect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:00
S87	10469	(plasma adj treat\$4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:01

S88	110	S87 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:19
S89	426	S87 with step	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:06
S90	3	S87 with etch with inert	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:19
S91	3	S87 with etch with inert adj gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:19
S92	213	S87 with inert adj gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:20
S93	213	(S87 with inert adj gas).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:21
S94	4	S87 with inert adj gas with poly	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:21
S95	2	S87 with inert adj gas with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:21
S96	3	S87 with inert adj gas with in-situ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:22
S97	213	(S87 with inert adj gas).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:25

S98	0	S97 with insitu	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:23
S99	3	S97 with in-situ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:23
S10 3	7	insitu with etch with clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:43
S10 4	4	S2 and insitu	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:29
S10 5	3	inert adj plasma adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:31
S10 6	2	(inert adj plasma adj etch).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:31
S10 8	1	S97 with overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:27
S11 0	748	134/1.2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:28
S11 1	20	S110 and overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:30
S11 2	9	S111 and inert	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:34

S11 3	40	S110 and neutral\$5 with charg\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:45
S11 4	0	(S110 and neutral\$5 with charg\$4). ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:35
S11 5	7	S110 and neutral\$5 adj charg\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:47
S11 6	2	S110 and neutral\$5 adj charg\$4 adj surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:56
S11 7	0	S110 and neutral\$5 adj charg\$4 adj before adj overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:50
S11 8	0	neutral\$5 adj charg\$4 adj before adj overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:50
S11 9	0	neutral\$5 adj charg\$4 with before adj overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:50
S12 0	0	S110 and remov\$4 adj charg\$4 with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:51
S12 1	1323	remov\$4 adj charg\$4 with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:51
S12 2	42	remov\$4 adj charg\$4 with surface and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:55

S12 3	0	remov\$4 adj charg\$4 with surface and overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:51
S12 4	0	balanc\$3 adj charg\$4 with inert adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:55
S12 5	0	alter adj charg\$4 with inert adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:56
S12 6	0	alter adj charg\$4 with inert with plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:57
S12 7	204	charg\$4 with inert with plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:57
S12 9	45	S127 and local\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:00
S13 0	15	S127 and local\$4 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:01
S13 1	234	wafer adj charging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:01
S13 2	72	wafer adj charging and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:02
S13 3	72	wafer adj charging and etch not apperatus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:02

S13 4	30	wafer adj charging and etch not apparatus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:03
S13 5	0	inert adj plasma with reduce adj charging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:04
S13 6	0	inert adj plasma with balance adj charging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:04
S13 7	0	inert adj plasma with balance with charging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:04
S13 8	0	Ar adj plasma with charging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:05
S13 9	243	plasma adj charging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:05
S14 0	127	S139 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:09
S14 1	2	"6451647".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:10
S14 2	0	"6451647".pn. and charging	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:10
S14 3	1	"6451647".pn. and charge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:24

S14 4	33	stringer adj removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:25
S14 5	21	S144 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:27
S14 6	1	S144 and plasma and inert	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:28
S14 7	23	("20020048910"   "5924000"   "6013570"   "6020243"   "6074956"   "6159794"   "6283131"   "6290806"   "6291356"   "6291361"   "6300203"   "6322714"   "6342165"   "6348373").PN. OR ("6451647").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:51
S14 8	0	S147 with charg\$4	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:42
S14 9	0	S147 with string\$4	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:42
S15 0	0	S147 with inert\$4	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:42
S15 1	0	S147 with inert	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:42
S15 2	0	S147 with plasma	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:42
S15 3	0	S147 with etch	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:42
S15 4	0	"342".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:51
S15 5	1	"6759342".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 14:56
S15 6	17	step with etch\$4 with avoid\$4 with string\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:59



S15 7	84	(string\$4 with treat\$5 with \$3move\$4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:01
S15 8	0	(S157 with etch).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:01
S15 9	1	(S157 with etch\$4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:02
S16 0	0	S157 with neutral\$4 with charg\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:02
S16 1	0	neutral\$4 adj charg\$4 with string\$4 with treat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:03
S16 2	5351	string\$4 with treat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:04
S16 3	0	string\$4 adj treat\$5 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:04
S16 4	15	neutral\$4 adj charg\$4 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:23
S16 5	8648	inert adj gas with plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:24
S16 6	1125	inert adj gas with plasma with etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:24

S16 7	352	(inert adj gas with plasma with etch\$4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:24
S16 8	2	(inert adj gas with plasma with etch\$4 with poly).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:25
S16 9	0	(inert adj gas with plasma with ion adj charg4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:25
S17 0	0	(inert adj gas with ion adj charg4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:26
S17 1	0	(inert adj gas with adjust\$4 with charg4).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:26
S17 2	0	(inert adj gas with adjust\$4 with charg4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:26
S17 3	90	(inert adj gas with adjust\$4 with charg\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:28
S17 4	0	inert adj gas with adjust\$4 with charg\$4 with etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:26
S17 5	0	S173 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:27
S17 6	3	S173 with semiconduct\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:28

S17 7	101	resist with inert with plasma with gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:29
S17 8	8	resist adj remov\$4 with inert with plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:30
S17 9	1	insit\$3 with inert with plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:32
S18 0	2	"5,665,203".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 11:34
S18 1	27	"5,665,203"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 12:17
S18 4	1	"6333271".pn.	USPAT	OR	OFF	2005/04/25 12:21
S18 5	1	"6333271".pn.	USPAT	OR	OFF	2005/04/25 12:20
S18 6	1	"6777340"	USPAT	OR	OFF	2005/04/25 12:24
S18 7	0	"10714207"	USPAT	OR	OFF	2005/04/25 12:30
S18 8	1	"6818553"	USPAT	OR	OFF	2005/04/25 12:40
S18 9	1	"6812044"	USPAT	OR	OFF	2005/04/25 12:45
S19 0	57	polysi\$5 with preferen\$5 with etch\$4	USPAT	OR	OFF	2005/04/25 12:48
S19 1	3	(polysi\$5 with preferen\$5 with etch\$4).ab.	USPAT	OR	OFF	2005/04/25 12:48
S19 3	0	11/033912	USPAT	OR	OFF	2005/04/25 12:52
S19 4	0	11/033912.ap.	USPAT	OR	OFF	2005/04/25 12:52
S19 5	4	"033912"	USPAT	OR	OFF	2005/04/25 12:52
S19 6	1	"6812044"	USPAT	OR	OFF	2005/04/25 13:02

S19 7	5	"6497993"	USPAT	OR	OFF	2005/04/25 13:41
S19 8	3	"6333271"	USPAT	OR	OFF	2005/04/25 13:44
S19 9	7	"6235653"	USPAT	OR	OFF	2005/04/25 13:47
S20 0	2	"6524938"	USPAT	OR	OFF	2005/04/25 13:50
S20 1	1	"6867084"	USPAT	OR	OFF	2005/04/25 13:53
S20 4	0	"6884736"	USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/04/25 13:54
S20 5	0	"6884736".pn.	USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/04/25 14:05
S20 6	5	"6528363"	USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/04/25 14:05

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	"6656796"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:44
S1	24945	charg\$4 and inert and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 07:13
S2	932	charg\$4 same inert same plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:15
S3	27	charg\$4 same inert same plasma with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 12:24
S7	213	S2 and (N and P)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:46
S8	1	S7 and (etch.ab.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:26
S9	53	S7 and poly	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:27
S10	133	S7 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:27
S11	24	S10 and poly	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:29
S12	6	S10 and poly and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:29

S13	4139	etch with N and P	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:30
S14	1950	etch with N with P	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:30
S15	7138	etch same N same P	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:30
S16	46	etch with N with P and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:31
S17	46	etch with N with P and S1 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:32
S18	1	S16 and 438/714.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:45
S19	2	S3 and 438/714.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:45
S20	1261	poly with gate with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:46
S21	28	S1 and poly with gate with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:52
S22	21	S1 and poly with gate with etch not anti-reflective	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:58

S23	2869	438/714.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:58
S24	3	S22 and 438/714.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:00
S25	145	S23 and gate with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 14:57
S27	20	S23 and stringers	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 11:49
S28	2	S27 and improvement	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 09:17
S36	37	avoid and preferential with RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:44
S37	96	avoid\$4 and preferential\$2 with RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:01
S38	5	avoid\$4 with preferential\$2 with RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:42
S39	98	S2 and (N with P)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:49
S44	2	"5665203".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:54
S45	2	"5336365".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:55

S46	2	"6759342".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:57
S47	17	charg\$4 with inbalanc\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:58
S48	4770994	uneven with etch\$4 adj\$6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:59
S49	4191229	uneven with etch\$4 adj\$6 gate with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 10:03
S50	319994	S49 and "438"/\$.ccls. or "257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:16
S51	4583825	uneven adj\$2 etch\$4 adj\$6 gate with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:00
S55	1065	plasma with treat\$5 with charg\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:16
S56	373440	"438"/\$.ccls. or "257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:16
S58	23	plasma with treat\$5 with charg\$4 same etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:57
S59	9	plasma with inert\$3 with charg\$4 same etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:28